

isc N-Channel MOSFET Transistor

2SK850

DESCRIPTION

- Drain Current $-I_D=40A @ T_C=25^\circ C$
- Drain Source Voltage-
: $V_{DSS}=100V(\text{Min})$

APPLICATIONS

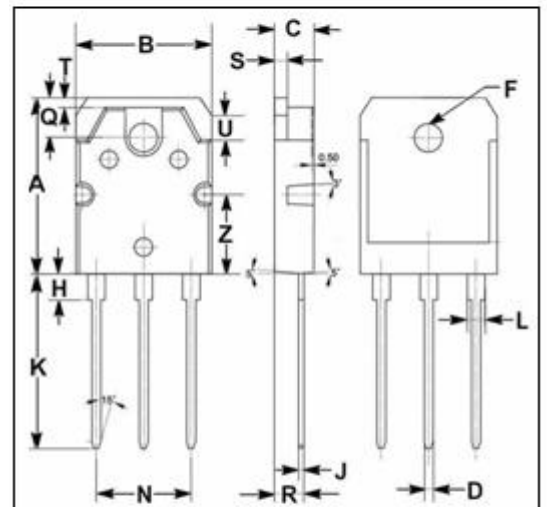
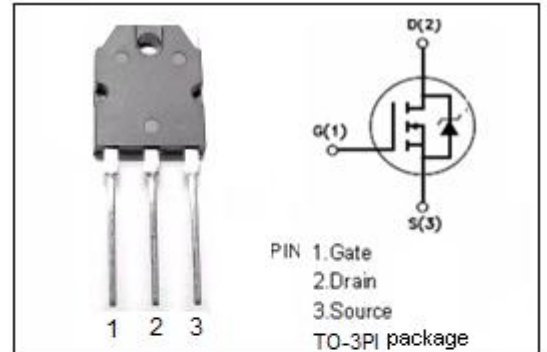
- Designed for use in switch mode power supplies and general purpose applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	100	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $T_C=25^\circ C$	40	A
P_{tot}	Total Dissipation@ $T_C=25^\circ C$	125	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance,Junction to Case	1.67	$^\circ C/W$
$R_{th\ j-a}$	Thermal Resistance,Junction to Ambient	62.5	$^\circ C/W$



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.50	15.70
C	4.40	4.60
D	0.90	1.10
F	3.20	3.40
H	2.90	3.10
J	0.50	0.70
K	19.90	20.10
L	1.90	2.10
N	10.80	11.00
Q	4.40	4.60
R	3.30	3.35
S	1.40	1.60
T	1.00	1.20
U	2.10	2.30
Z	8.90	9.10

isc N-Channel Mosfet Transistor**2SK850****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 10mA	100			V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =0; I _D = 1mA	2.0		4.0	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = 10V; I _D =20A			0.06	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±16V; V _{DS} = 0			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =100V; V _{GS} = 0			0.1	mA